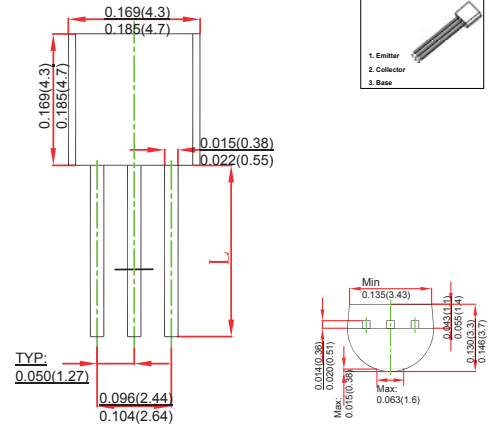


TO-92 Plastic-Encapsulate Transistors
FEATURES

- Excellent hFE Linearity
- Low Noise
- Complementary to KTC3198
- TRANSISTOR (PNP)

MECHANICAL DATA

- Case style:TO-92 molded plastic
- Mounting position:any

TO-92

MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CB0}	Collector-Base Voltage	-50	V
V _{CEO}	Collector-Emitter Voltage	-50	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current -Continuous	-150	mA
P _D	Collector Power Dissipation	625	mW
R _{θ JA}	Thermal Resistance from Junction to Ambient	200	°C /W
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55 ~+150	°C

ELECTRICAL CHARACTERISTICS Ta =25 °C unless otherwise specified

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =-100μA, I _E =0	-50			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =-1mA, I _B =0	-50			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-100μA, I _C =0	-5			V
Collector cut-off current	I _{CBO}	V _{CB} =-50V, I _E =0			-0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =-5V, I _C =0			-0.1	μA
DC current gain	h _{FE(1)}	V _{CE} =-6V, I _C =-2mA	70		400	
	h _{FE(2)}	V _{CE} =-6V, I _C =-150mA	25			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-100mA, I _B =-10mA			-0.3	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =-100mA, I _B =-10mA			-1.1	V
Transition frequency	f _T	V _{CE} =-10V, I _C =-1mA	80			MHz
Collector output capacitance	C _{ob}	V _{CB} =-10V, I _E =0, f=1MHz			7	pF
Noise figure	NF	V _{CE} =-6V, I _C =-0.1mA, f=1KHZ, R _g =10KΩ			10	dB

CLASSIFICATION OF h_{FE(1)}

Rank	O	Y	GR
Range	70-140	120-240	200-400